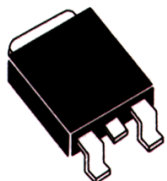




CJD200 NPN
CJD210 PNP

COMPLEMENTARY SILICON
POWER TRANSISTOR

MPAK POWER!TM



DPAK CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD200, CJD210 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for high current amplifier applications.

MAXIMUM RATINGS ($T_C=25^{\circ}C$)

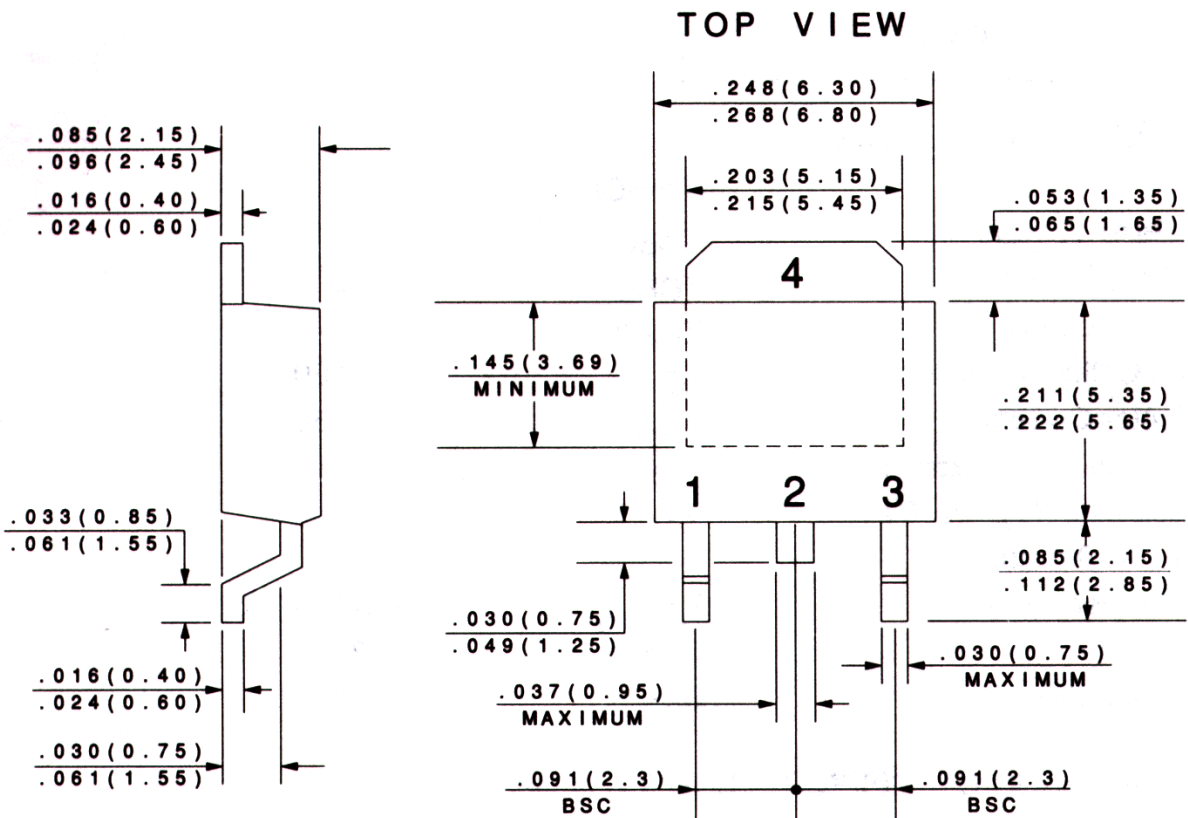
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	8.0	V
Continuous Collector Current	I_C	5.0	A
Peak Collector Current	I_{CM}	10	A
Base Current	I_B	1.0	A
Power Dissipation ($T_C=25^{\circ}C$)	P_D	12.5	W
Power Dissipation ($T_A=25^{\circ}C$)	P_D	1.4	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}C$
Thermal Resistance	θ_{JC}	10	$^{\circ}C/W$
Thermal Resistance	θ_{JA}	89.3	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=40V$		100	nA
I_{CBO}	$V_{CB}=40V, T_C=125^{\circ}C$		100	μA
I_{EBO}	$V_{EB}=8.0V$		100	nA
BV_{CEO}	$I_C=10mA$	25		V
$V_{CE(SAT)}$	$I_C=500mA, I_B=50mA$		0.3	V
$V_{CE(SAT)}$	$I_C=2.0A, I_B=200mA$		0.75	V
$V_{CE(SAT)}$	$I_C=5.0A, I_B=1.0A$		1.8	V
$V_{BE(SAT)}$	$I_C=5.0A, I_B=1.0A$		2.5	V
$V_{BE(ON)}$	$V_{CE}=1.0V, I_C=2.0A$		1.6	V
h_{FE}	$V_{CE}=1.0V, I_C=500mA$	70		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=1.0V, I_C=2.0A$	45	180	
h_{FE}	$V_{CE}=2.0V, I_C=5.0A$	10		
f_T	$V_{CE}=10V, I_C=100mA, f=10MHz$	65		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz (CJD200)$		80	pF
C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz (CJD210)$		120	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR